

FIG. 1

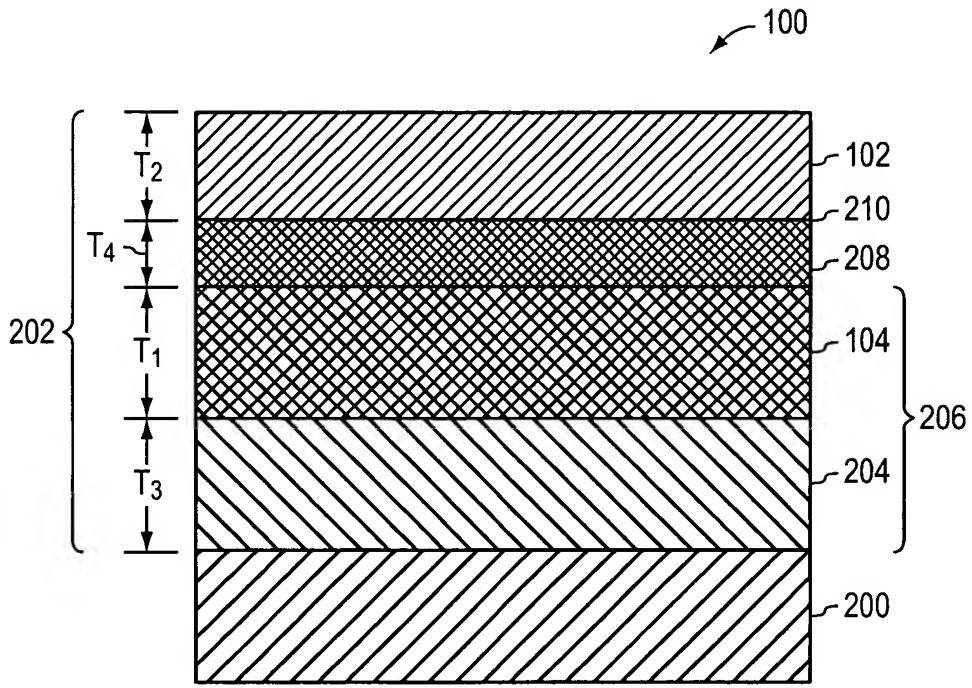
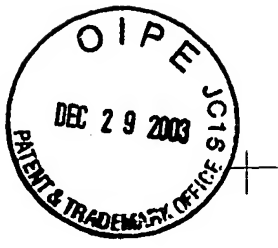
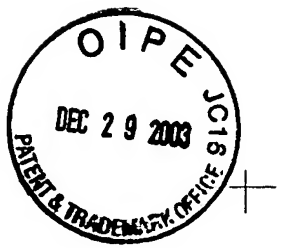


FIG. 2





"Gate Material for Semiconductor Device
Fabrication" by Lochtefeld et al.
Serial No. 10/691,007 Filed 10/22/2003
Natasha C. Us (617) 310-8327
Reg. No. 44,381
Atty Docket No. ASC-060

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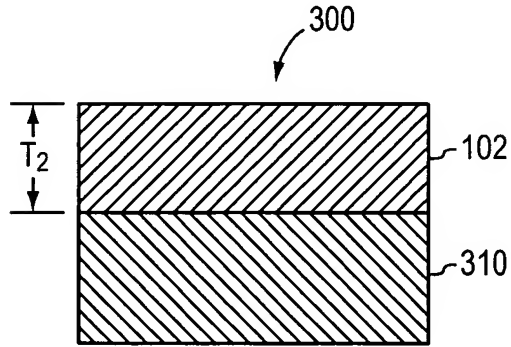


FIG. 3



"Gate Material for Semiconductor Device
Fabrication" by Lochtefeld et al.
Serial No. 10/691,007 Filed 10/22/2003
Natasha C. Us (617) 310-8327
Reg. No. 44,381
Atty Docket No. ASC-060

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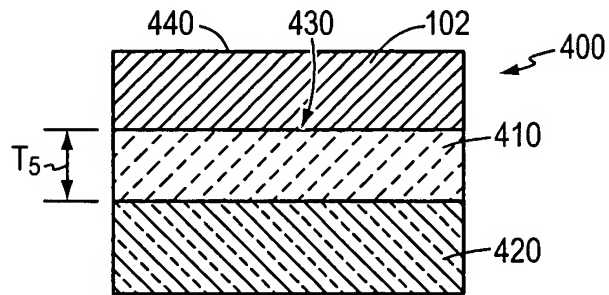


FIG. 4

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"Gate Material for Semiconductor Device
Fabrication" by Lochtefeld et al.
Serial No. 10/691,007 Filed 10/22/2003
Natasha C. Us (617) 310-8327
Reg. No. 44,381
Atty Docket No. ASC-060

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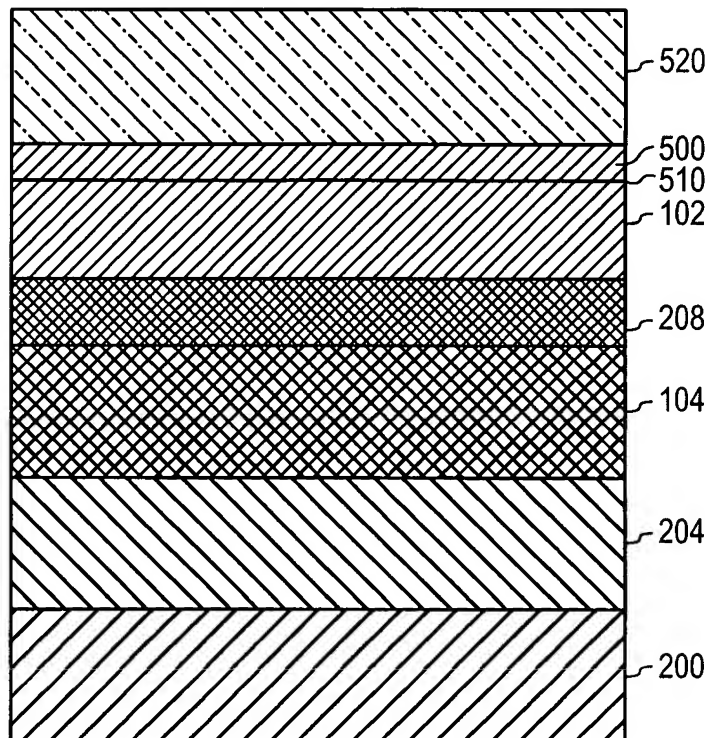


FIG. 5



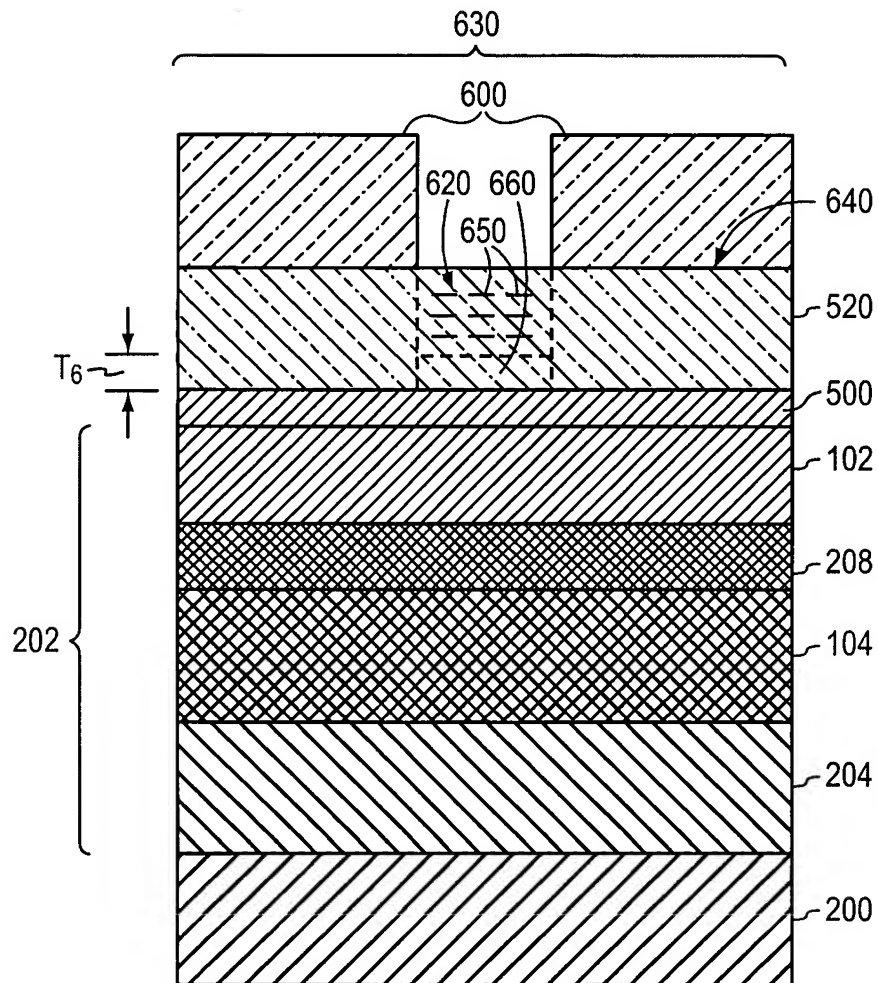


FIG. 6



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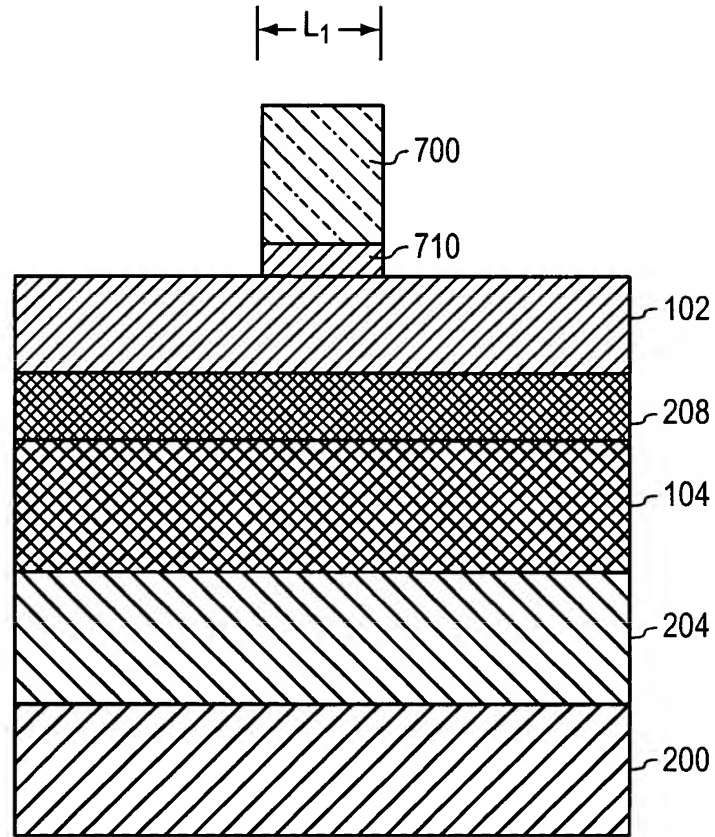


FIG. 7



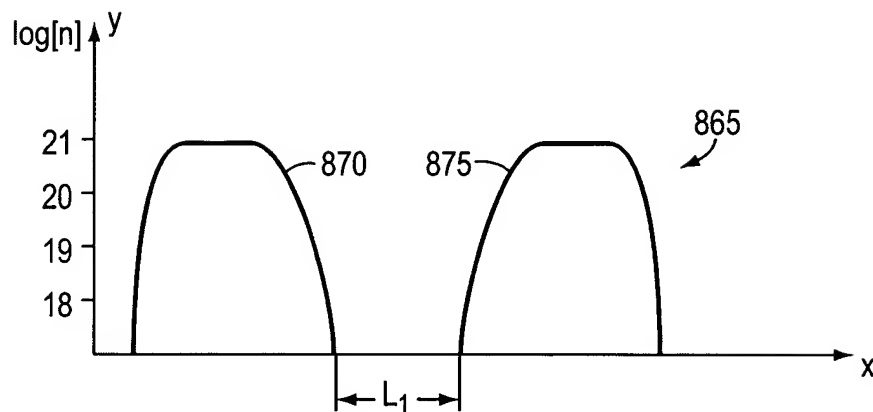


FIG. 8B

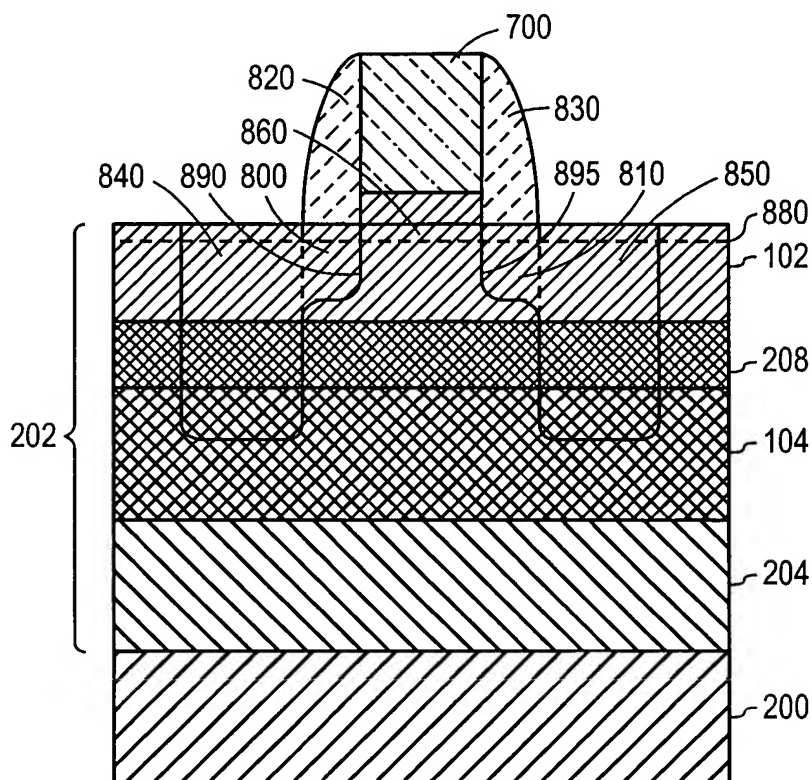


FIG. 8A

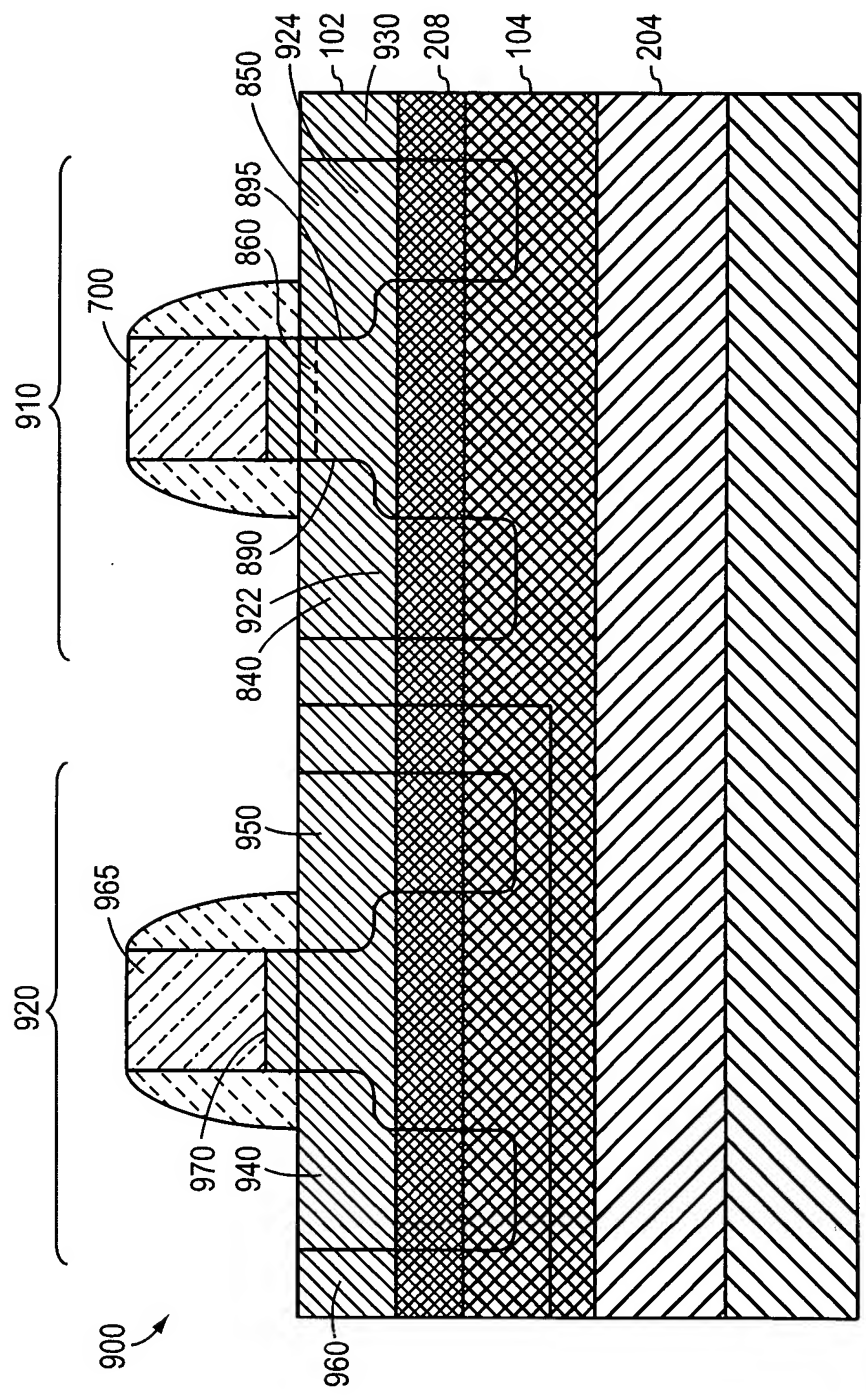


FIG. 9

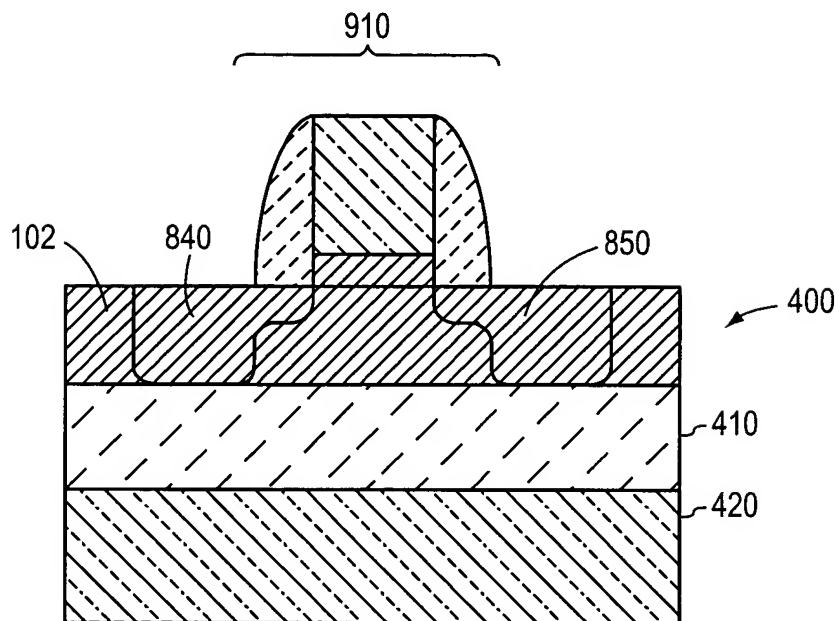


FIG. 10